Ultra fast low-loss controlled avalanche rectifiers

BYD77 series

FEATURES

- Glass passivated
- High maximum operating temperature
- Low leakage current
- Excellent stability
- Guaranteed avalanche energy absorption capability
- Shipped in 8 mm embossed tape
- Smallest surface mount rectifier outline.

DESCRIPTION

Cavity free cylindrical glass SOD87 package through Implotec™(1) technology. This package is hermetically sealed and fatigue free as coefficients of expansion of all used parts are matched.

(1) Implotec is a trademark of Philips.

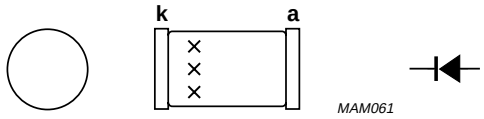


Fig.1 Simplified outline (SOD87) and symbol.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage				
	BYD77A		–	50	V
	BYD77B		–	100	V
	BYD77C		–	150	V
	BYD77D		–	200	V
	BYD77E		–	250	V
	BYD77F		–	300	V
	BYD77G		–	400	V
V_R	continuous reverse voltage				
	BYD77A		–	50	V
	BYD77B		–	100	V
	BYD77C		–	150	V
	BYD77D		–	200	V
	BYD77E		–	250	V
	BYD77F		–	300	V
	BYD77G		–	400	V
$I_{F(AV)}$	average forward current	T_{tp} = 105 °C; see Figs 2 and 3; averaged over any 20 ms period; see also Figs 10 and 11			
	BYD77A to D		–	2.00	A
	BYD77E to G		–	1.85	A
$I_{F(AV)}$	average forward current	T_{amb} = 60 °C; PCB mounting (see Fig.16); see Figs 4 and 5; averaged over any 20 ms period; see also Figs 10 and 11			
	BYD77A to D		–	0.85	A
	BYD77E to G		–	0.80	A

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
I_{FRM}	repetitive peak forward current	T_{tp} = 105 °C; see Figs 6 and 7			
	BYD77A to D		–	15	A
	BYD77E to G		–	13	A
I_{FRM}	repetitive peak forward current	T_{amb} = 60 °C; see Figs 8 and 9			
	BYD77A to D		–	8.5	A
	BYD77E to G		–	8.0	A
I_{FSM}	non-repetitive peak forward current	t = 10 ms half sine wave; $T_j = T_{j\,max}$ prior to surge; $V_R = V_{RRMmax}$	–	25	A
E_{RSM}	non-repetitive peak reverse avalanche energy	L = 120 mH; T_j = 25 °C prior to surge; inductive load switched off	–	10	mJ
T_{stg}	storage temperature		–65	+175	°C
T_j	junction temperature		–65	+175	°C

ELECTRICAL CHARACTERISTICS

T_j = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_F	forward voltage	I_F = 1 A; $T_j = T_{j\,max}$; see Figs 12 and 13				
	BYD77A to D		–	–	0.75	V
	BYD77E to G		–	–	0.83	V
V_F	forward voltage	I_F = 1 A; see Figs 12 and 13				
	BYD77A to D		–	–	0.98	V
	BYD77E to G		–	–	1.05	V
$V_{(BR)R}$	reverse avalanche breakdown voltage	I_R = 0.1 mA				
	BYD77A		55	–	–	V
	BYD77B		110	–	–	V
	BYD77C		165	–	–	V
	BYD77D		220	–	–	V
	BYD77E		275	–	–	V
	BYD77F		330	–	–	V
	BYD77G		440	–	–	V
I_R	reverse current	$V_R = V_{RRMmax}$; see Fig.14	–	–	1	µA
		$V_R = V_{RRMmax}$; T_j = 165 °C; see Fig.14	–	–	100	µA
t_{rr}	reverse recovery time	when switched from I_F = 0.5 A to I_R = 1 A; measured at I_R = 0.25 A; see Fig.18				
	BYD77A to D		–	–	25	ns
	BYD77E to G		–	–	50	ns

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
C_d	diode capacitance	f = 1 MHz; V_R = 0 V; see Fig.15				
	BYD77A to D		–	50	–	pF
	BYD77E to G		–	40	–	pF
$\left\|\frac{dI_R}{dt}\right\|$	maximum slope of reverse recovery current	when switched from I_F = 1 A to $V_R \geq$ 30 V and dI_F/dt = –1 A/µs; see Fig.17				
	BYD77A to D		–	–	4	A/µs
	BYD77E to G		–	–	5	A/µs

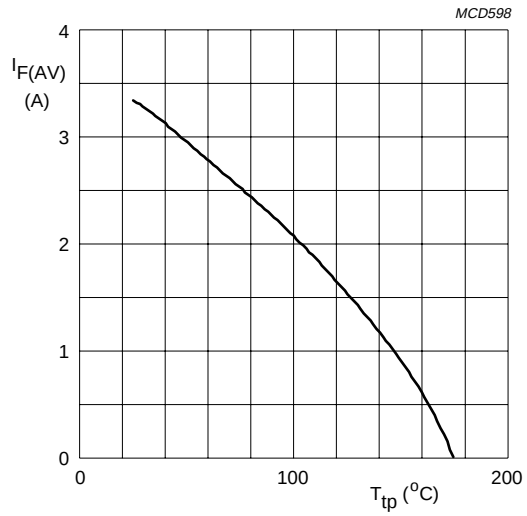
THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}tp}$	thermal resistance from junction to tie-point		30	K/W
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	150	K/W

Note

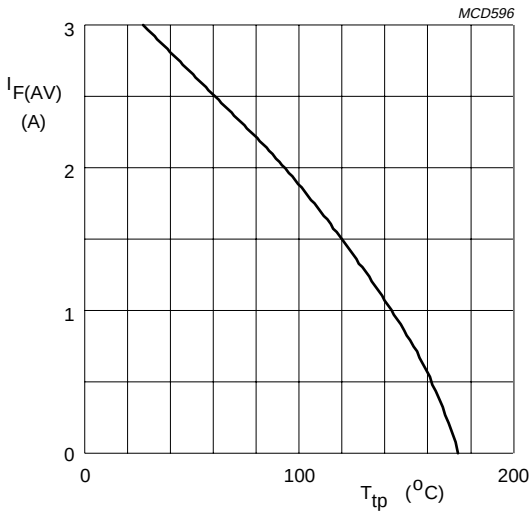
1. Device mounted on an epoxy-glass printed-circuit board, 1.5 mm thick; thickness of Cu-layer ≥40 µm, see Fig.16. For more information please refer to the *"General Part of associated Handbook"*.

GRAPHICAL DATA



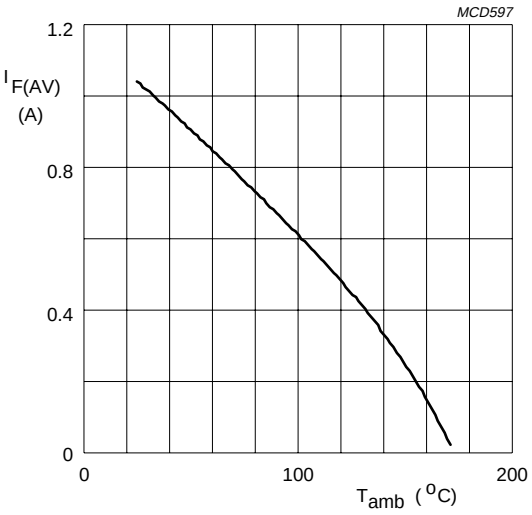
BYD77A to D
a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.
Switched mode application.

Fig.2 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).



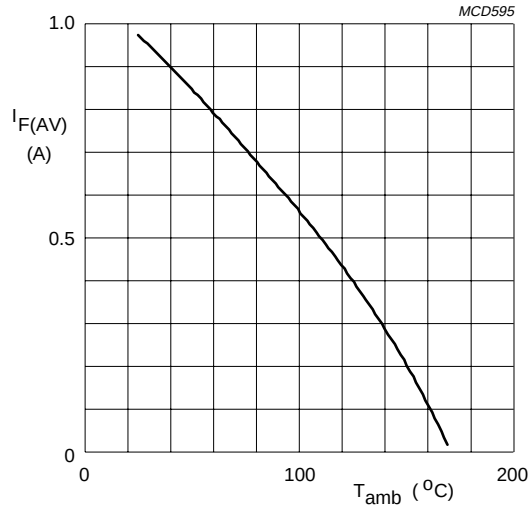
BYD77E to G
a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.
Switched mode application.

Fig.3 Maximum permissible average forward current as a function of tie-point temperature (including losses due to reverse leakage).



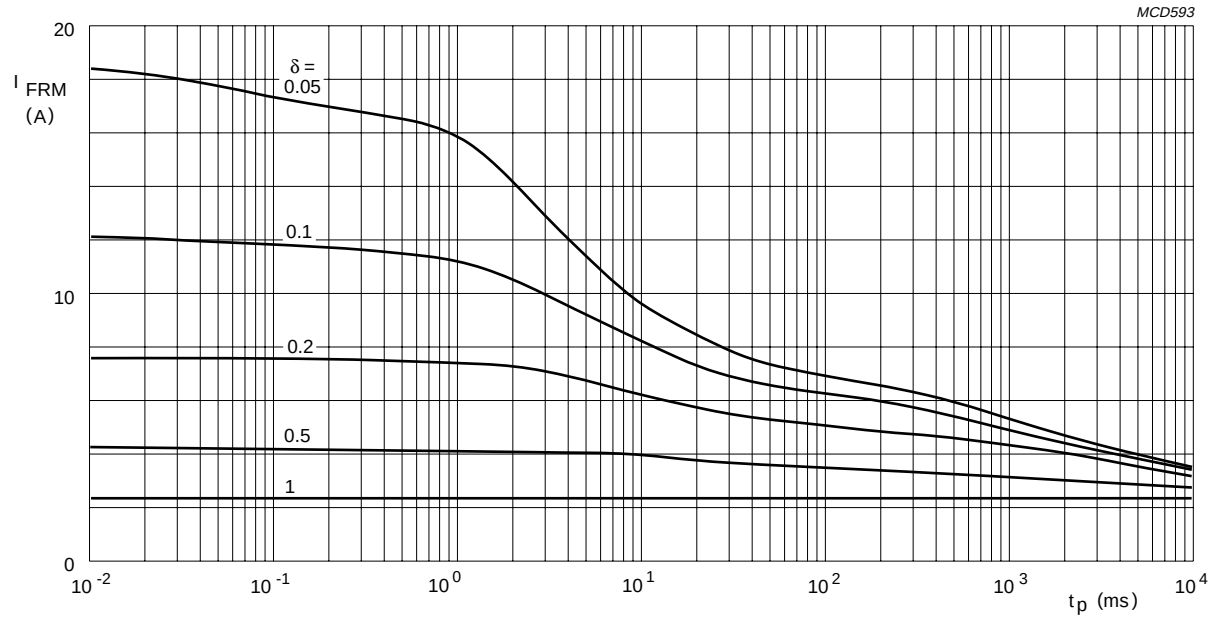
BYD77A to D
a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.
Device mounted as shown in Fig.16.
Switched mode application.

Fig.4 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).



BYD77E to G
a = 1.42; $V_R = V_{RRMmax}$; δ = 0.5.
Device mounted as shown in Fig.16.
Switched mode application.

Fig.5 Maximum permissible average forward current as a function of ambient temperature (including losses due to reverse leakage).

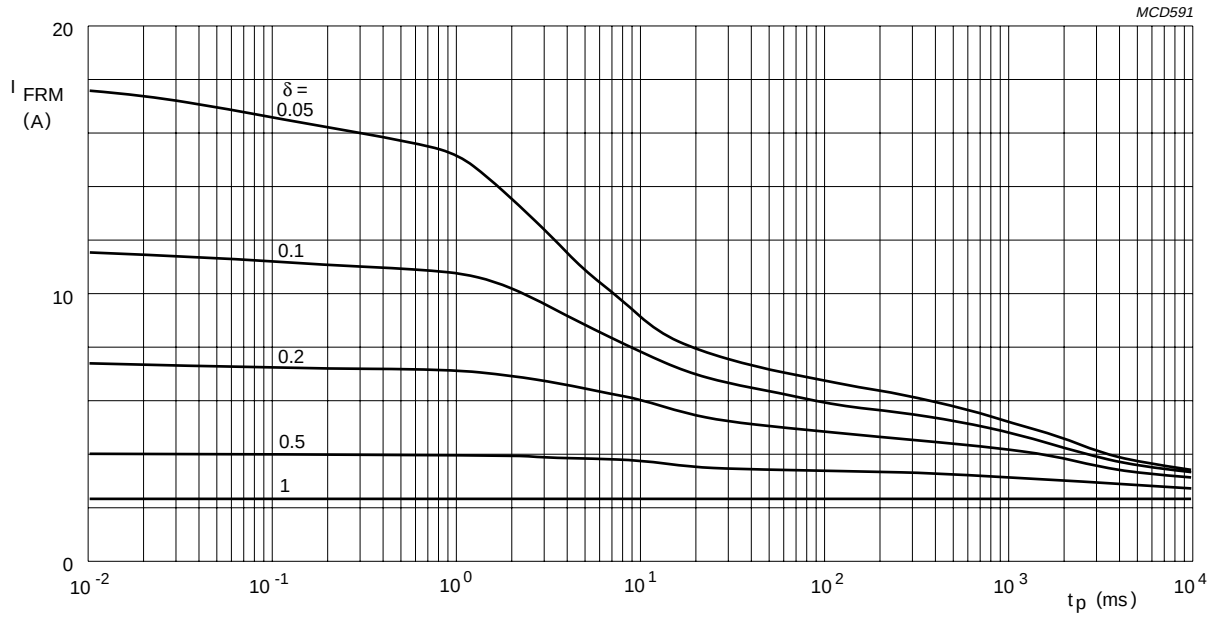


BYD77A to D

T_{tp} = 105 °C; $R_{th\ j\text{-}tp}$ = 30 K/W.

V_{RRMmax} during 1 – δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 200 V.

Fig.6 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

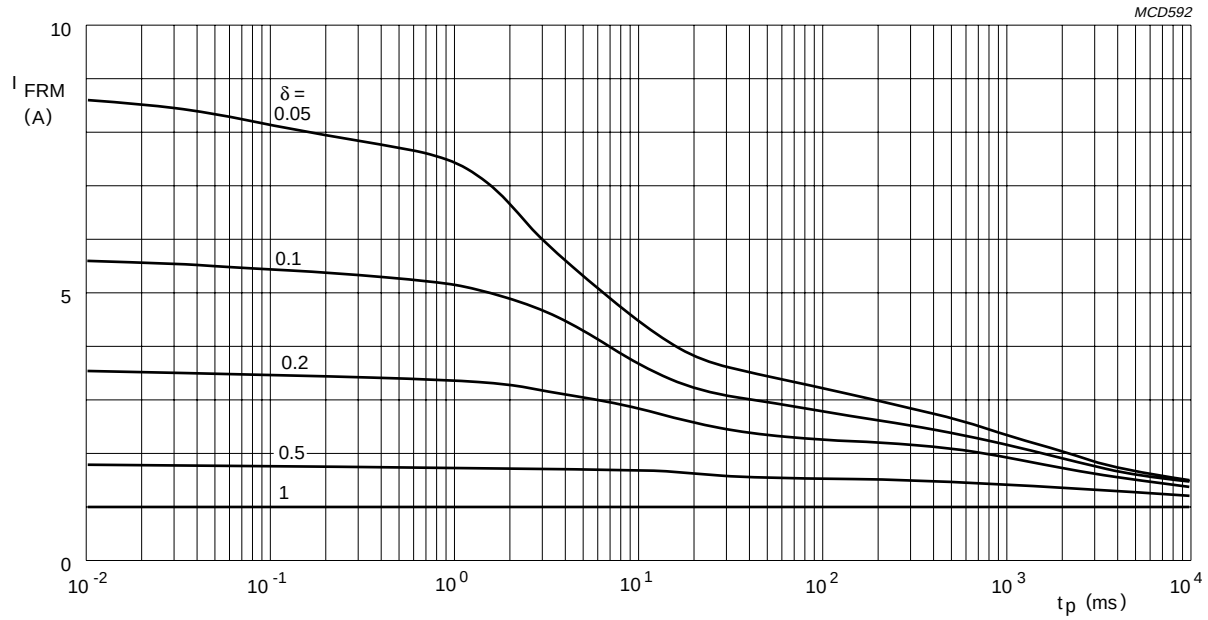


BYD77E to G

T_{tp} = 105°C; $R_{th\ j\text{-}tp}$ = 30 K/W.

V_{RRMmax} during 1 – δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 400 V.

Fig.7 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

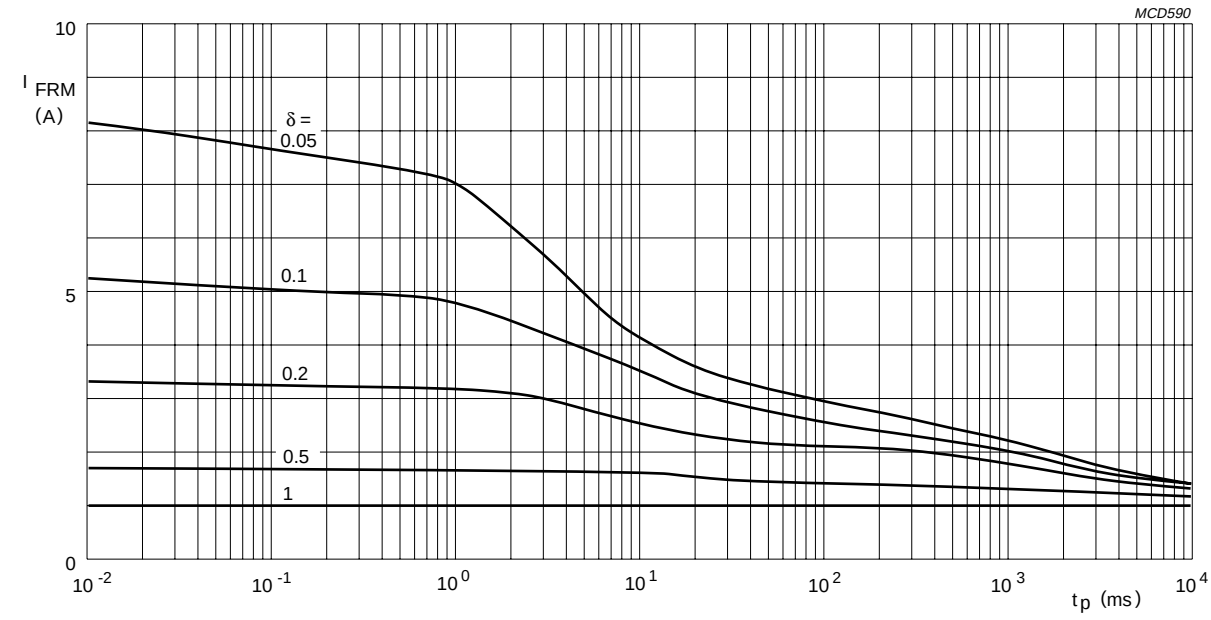


BYD77A to D

T_{amb} = 60 °C; $R_{th\ j\text{-}a}$ = 150 K/W.

V_{RRMmax} during 1 – δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 200 V.

Fig.8 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.

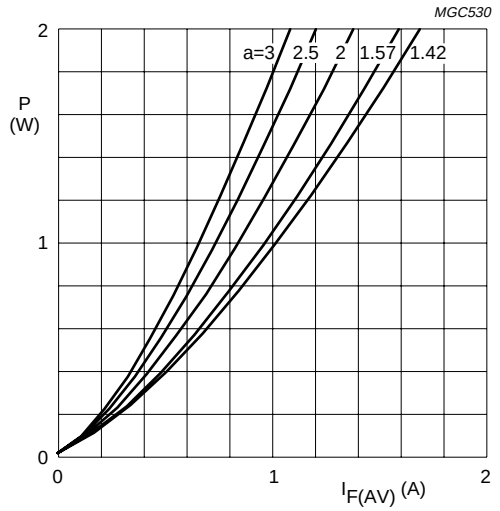


BYD77E to G

T_{amb} = 60 °C; $R_{th\ j\text{-}a}$ = 150 K/W.

V_{RRMmax} during 1 – δ; curves include derating for $T_{j\ max}$ at V_{RRM} = 400 V.

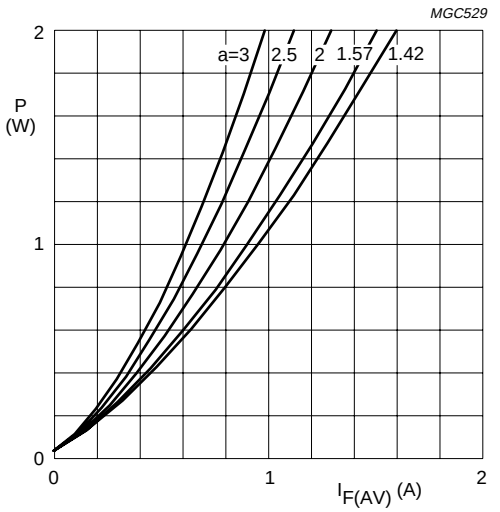
Fig.9 Maximum repetitive peak forward current as a function of pulse time (square pulse) and duty factor.



BYD77A to D

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$; $\delta = 0.5$.

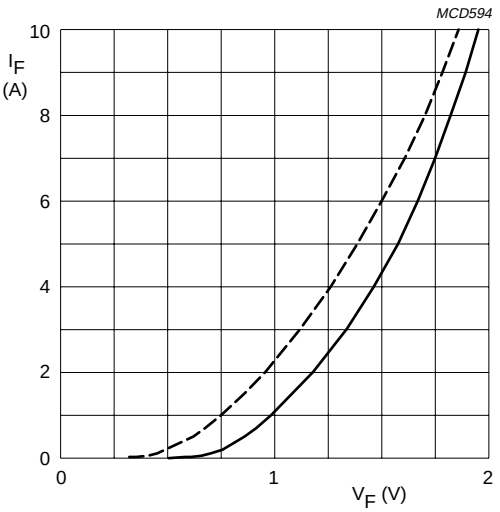
Fig.10 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.



BYD77E to G

$a = I_{F(RMS)}/I_{F(AV)}$; $V_R = V_{RRMmax}$; $\delta = 0.5$.

Fig.11 Maximum steady state power dissipation (forward plus leakage current losses, excluding switching losses) as a function of average forward current.

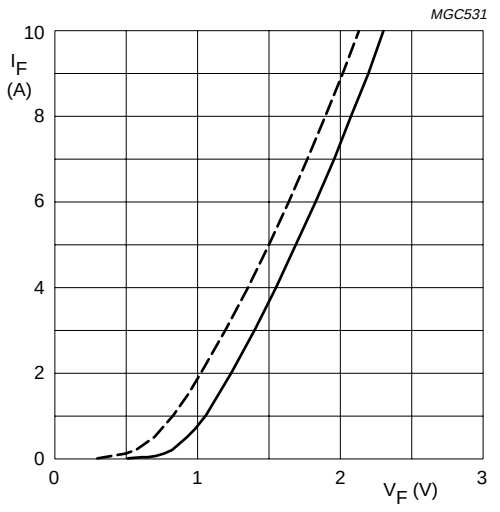


BYD77A to D

Dotted line: $T_j = 175$ °C.

Solid line: $T_j = 25$ °C.

Fig.12 Forward current as a function of forward voltage; maximum values.

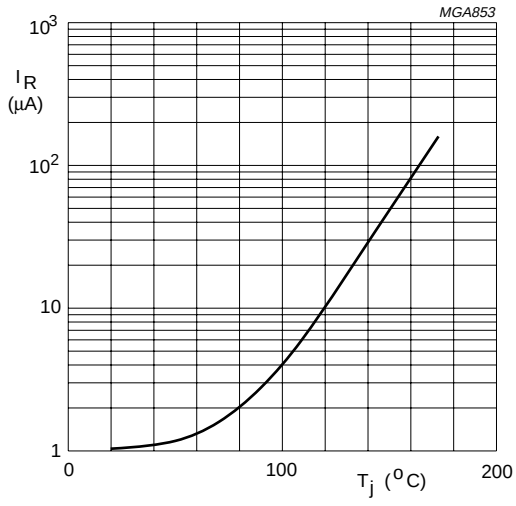


BYD77E to G

Dotted line: $T_j = 175$ °C.

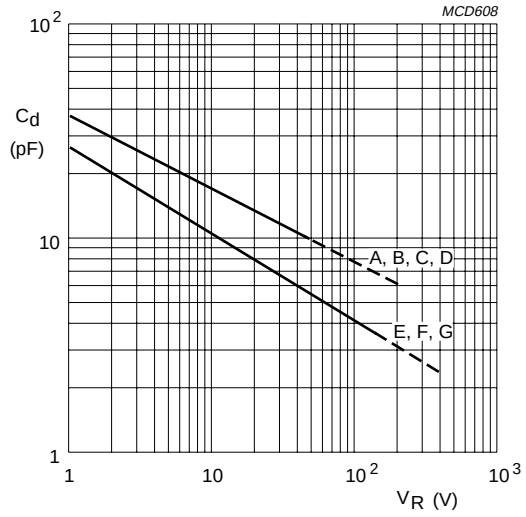
Solid line: $T_j = 25$ °C.

Fig.13 Forward current as a function of forward voltage; maximum values.



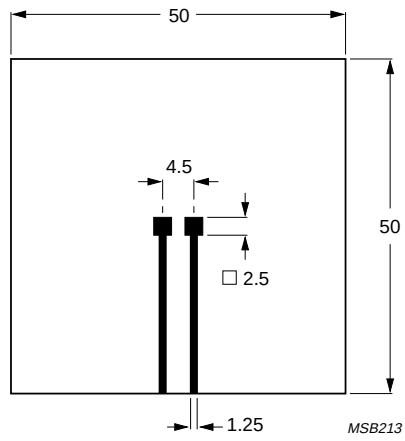
$V_R = V_{RRMmax}$.

Fig.14 Reverse current as a function of junction temperature; maximum values.



f = 1 MHz; T_j = 25 °C.

Fig.15 Diode capacitance as a function of reverse voltage; typical values.



Dimensions in mm.

Fig.16 Printed-circuit board for surface mounting.

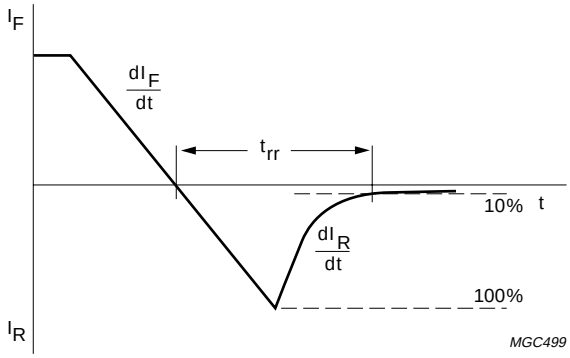
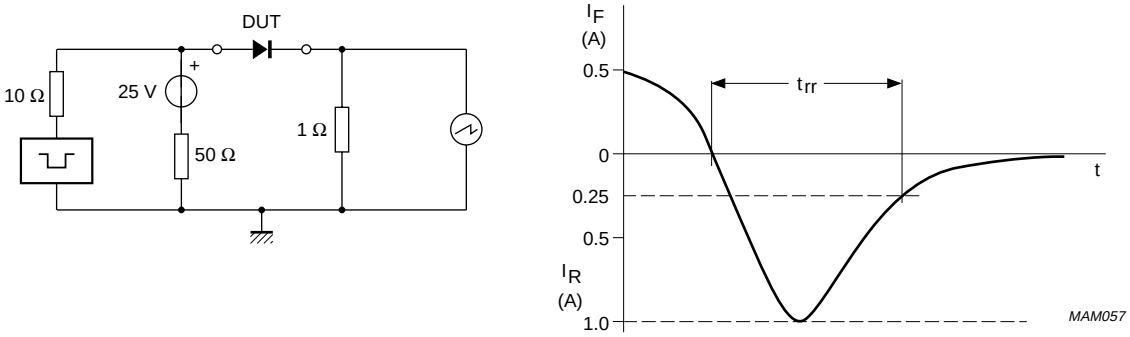


Fig.17 Reverse recovery definitions.

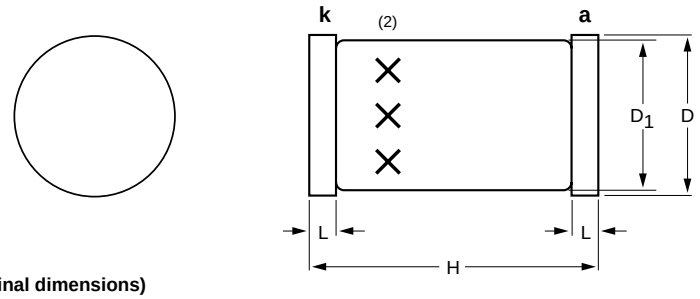


Input impedance oscilloscope: 1 MΩ, 22 pF; $t_r \leq 7$ ns.
Source impedance: 50 Ω; $t_r \leq 15$ ns.

Fig.18 Test circuit and reverse recovery time waveform and definition.

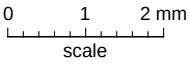
PACKAGE OUTLINE

Hermetically sealed glass surface mounted package;
Implotec™(1) technology; 2 connectors **SOD87**



DIMENSIONS (mm are the original dimensions)

UNIT	D	D1	H	L
mm	2.1 2.0	2.0 1.8	3.7 3.3	0.3



Notes

1. Implotec is a trademark of Philips.
2. The marking indicates the cathode.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOD87	100H03					~~99-03-31~~ 99-06-04

DEFINITIONS

Data Sheet Status	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
Limiting values	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
Application information	
Where application information is given, it is advisory and does not form part of the specification.	

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Philips Semiconductors – a worldwide company

Argentina: see South America

Australia: 3 Figtree Drive, HOMEBUSH, NSW 2140,
Tel. +61 2 9704 8141, Fax. +61 2 9704 8139

Austria: Computerstr. 6, A-1101 WIEN, P.O. Box 213,
Tel. +43 1 60 101 1248, Fax. +43 1 60 101 1210

Belarus: Hotel Minsk Business Center, Bld. 3, r. 1211, Volodarski Str. 6,
220050 MINSK, Tel. +375 172 20 0733, Fax. +375 172 20 0773

Belgium: see The Netherlands

Brazil: see South America

Bulgaria: Philips Bulgaria Ltd., Energoproject, 15th floor,
51 James Bourchier Blvd., 1407 SOFIA,
Tel. +359 2 68 9211, Fax. +359 2 68 9102

Canada: PHILIPS SEMICONDUCTORS/COMPONENTS,
Tel. +1 800 234 7381, Fax. +1 800 943 0087

China/Hong Kong: 501 Hong Kong Industrial Technology Centre,
72 Tat Chee Avenue, Kowloon Tong, HONG KONG,
Tel. +852 2319 7888, Fax. +852 2319 7700

Colombia: see South America

Czech Republic: see Austria

Denmark: Sydhavnsgade 23, 1780 COPENHAGEN V,
Tel. +45 33 29 3333, Fax. +45 33 29 3905

Finland: Sinikalliontie 3, FIN-02630 ESPOO,
Tel. +358 9 615 800, Fax. +358 9 6158 0920

France: 51 Rue Carnot, BP317, 92156 SURESNES Cedex,
Tel. +33 1 4099 6161, Fax. +33 1 4099 6427

Germany: Hammerbrookstraße 69, D-20097 HAMBURG,
Tel. +49 40 2353 60, Fax. +49 40 2353 6300

Hungary: see Austria

India: Philips INDIA Ltd, Band Box Building, 2nd floor,
254-D, Dr. Annie Besant Road, Worli, MUMBAI 400 025,
Tel. +91 22 493 8541, Fax. +91 22 493 0966

Indonesia: PT Philips Development Corporation, Semiconductors Division,
Gedung Philips, Jl. Buncit Raya Kav.99-100, JAKARTA 12510,
Tel. +62 21 794 0040 ext. 2501, Fax. +62 21 794 0080

Ireland: Newstead, Clonskeagh, DUBLIN 14,
Tel. +353 1 7640 000, Fax. +353 1 7640 200

Israel: RAPAC Electronics, 7 Kehilat Saloniki St, PO Box 18053,
TEL AVIV 61180, Tel. +972 3 645 0444, Fax. +972 3 649 1007

Italy: PHILIPS SEMICONDUCTORS, Via Casati, 23 - 20052 MONZA (MI),
Tel. +39 039 203 6838, Fax +39 039 203 6800

Japan: Philips Bldg 13-37, Kohnan 2-chome, Minato-ku,
TOKYO 108-8507, Tel. +81 3 3740 5130, Fax. +81 3 3740 5057

Korea: Philips House, 260-199 Itaewon-dong, Yongsan-ku, SEOUL,
Tel. +82 2 709 1412, Fax. +82 2 709 1415

Malaysia: No. 76 Jalan Universiti, 46200 PETALING JAYA, SELANGOR,
Tel. +60 3 750 5214, Fax. +60 3 757 4880

Mexico: 5900 Gateway East, Suite 200, EL PASO, TEXAS 79905,
Tel. +9-5 800 234 7381, Fax +9-5 800 943 0087

Middle East: see Italy

Netherlands: Postbus 90050, 5600 PB EINDHOVEN, Bldg. VB,
Tel. +31 40 27 82785, Fax. +31 40 27 88399

New Zealand: 2 Wagener Place, C.P.O. Box 1041, AUCKLAND,
Tel. +64 9 849 4160, Fax. +64 9 849 7811

Norway: Box 1, Manglerud 0612, OSLO,
Tel. +47 22 74 8000, Fax. +47 22 74 8341

Pakistan: see Singapore

Philippines: Philips Semiconductors Philippines Inc.,
106 Valero St. Salcedo Village, P.O. Box 2108 MCC, MAKATI,
Metro MANILA, Tel. +63 2 816 6380, Fax. +63 2 817 3474

Poland: Al.Jerozolimskie 195 B, 02-222 WARSAW,
Tel. +48 22 5710 000, Fax. +48 22 5710 001

Portugal: see Spain

Romania: see Italy

Russia: Philips Russia, Ul. Usatcheva 35A, 119048 MOSCOW,
Tel. +7 095 755 6918, Fax. +7 095 755 6919

Singapore: Lorong 1, Toa Payoh, SINGAPORE 319762,
Tel. +65 350 2538, Fax. +65 251 6500

Slovakia: see Austria

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South Africa: S.A. PHILIPS Pty Ltd., 195-215 Main Road Martindale,
2092 JOHANNESBURG, P.O. Box 58088 Newville 2114,
Tel. +27 11 471 5401, Fax. +27 11 471 5398

South America: Al. Vicente Pinzon, 173, 6th floor,
04547-130 SÃO PAULO, SP, Brazil,
Tel. +55 11 821 2333, Fax. +55 11 821 2382

Spain: Balmes 22, 08007 BARCELONA,
Tel. +34 93 301 6312, Fax. +34 93 301 4107

Sweden: Kottbygatan 7, Akalla, S-16485 STOCKHOLM,
Tel. +46 8 5985 2000, Fax. +46 8 5985 2745

Switzerland: Allmendstrasse 140, CH-8027 ZÜRICH,
Tel. +41 1 488 2741 Fax. +41 1 488 3263

Taiwan: Philips Semiconductors, 6F, No. 96, Chien Kuo N. Rd., Sec. 1,
TAIPEI, Taiwan Tel. +886 2 2134 2886, Fax. +886 2 2134 2874

Thailand: PHILIPS ELECTRONICS (THAILAND) Ltd.,
209/2 Sanpavuth-Bangna Road Prakanong, BANGKOK 10260,
Tel. +66 2 745 4090, Fax. +66 2 398 0793

Turkey: Yukari Dudullu, Org. San. Blg., 2.Cad. Nr. 28 81260 Umraniye,
ISTANBUL, Tel. +90 216 522 1500, Fax. +90 216 522 1813

Ukraine: PHILIPS UKRAINE, 4 Patrice Lumumba str., Building B, Floor 7,
252042 KIEV, Tel. +380 44 264 2776, Fax. +380 44 268 0461

United Kingdom: Philips Semiconductors Ltd., 276 Bath Road, Hayes,
MIDDLESEX UB3 5BX, Tel. +44 208 730 5000, Fax. +44 208 754 8421

United States: 811 East Arques Avenue, SUNNYVALE, CA 94088-3409,
Tel. +1 800 234 7381, Fax. +1 800 943 0087

Uruguay: see South America

Vietnam: see Singapore

Yugoslavia: PHILIPS, Trg N. Pasica 5/v, 11000 BEOGRAD,
Tel. +381 11 62 5344, Fax.+381 11 63 5777

For all other countries apply to: Philips Semiconductors,
International Marketing & Sales Communications, Building BE-p, P.O. Box 218,
5600 MD EINDHOVEN, The Netherlands, Fax. +31 40 27 24825

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